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Vishay Siliconix

Automotive N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.052			
I _D (A)	25			
Configuration	Single			
Package	TO-220			



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



G o	
N-Channel MOSFET	O S

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ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	150	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	I _D	25		
Continuous Drain Current	T _C = 125 °C		16		
Continuous Source Current (Diode Conduction) a		I _S	50	Α	
Pulsed Drain Current ^b	I _{DM}	65			
Single Pulse Avalanche Energy	L = 0.1 mH	I _{AS}	30		
Single Pulse Avalanche Current		E _{AS}	45	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	107	W	
Maximum Fower Dissipation -	T _C = 125 °C	гD	35	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.4	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static					l .	l .		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	150	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3	4	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 150 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 175 °C	-	-	250		
On-State Drain Current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.041	0.052		
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.106	Ω	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.138		
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 15 A	-	33	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	1886	2360		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	215	270	pF	
Reverse Transfer Capacitance	C _{rss}	1		-	97	125		
Total Gate Charge c	Qg			-	37.9	60		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 75 \text{ V}, I_{D} = 25 \text{ A}$	-	8.5	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	12.2	-		
Gate Resistance	R _g		f = 1 MHz	0.35	1.0	3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}				11	17		
Rise Time ^c	t _r	$\begin{aligned} V_{DD} &= 75 \text{ V, R}_L = 3 \Omega \\ I_D &\cong 25 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 1 \Omega \end{aligned}$		-	21	33	ns	
Turn-Off Delay Time c	t _{d(off)}			-	20	30		
Fall Time ^c	t _f]	-	12	20			
Source-Drain Diode Ratings and Characteristics b								
Pulsed Current ^a	I _{SM}				-	65	Α	
Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.85	1.5	V	

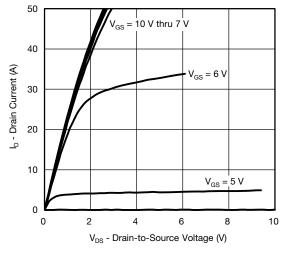
Notes

- a. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

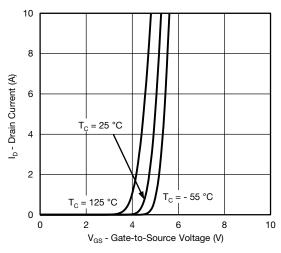
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



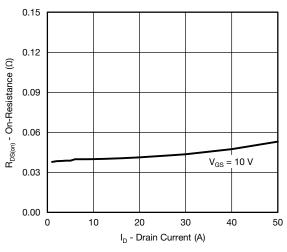
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



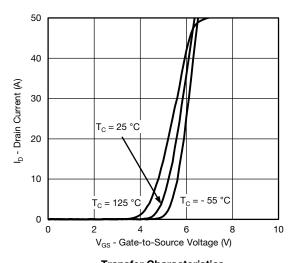
Output Characteristics



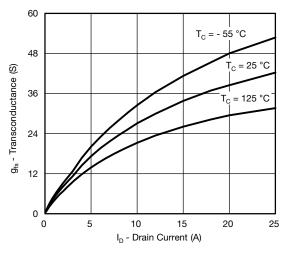
Transfer Characteristics



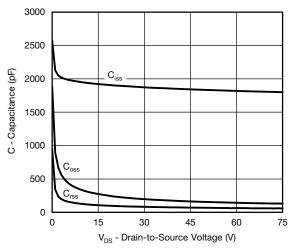
On-Resistance vs. Drain Current



Transfer Characteristics



Transconductance

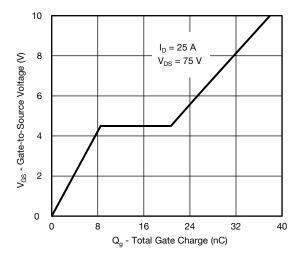


Capacitance

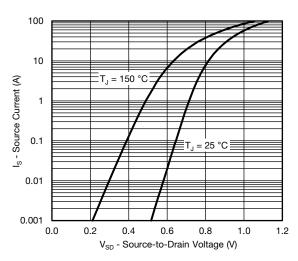
For technical questions, contact: automostechsu



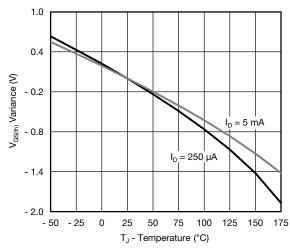
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



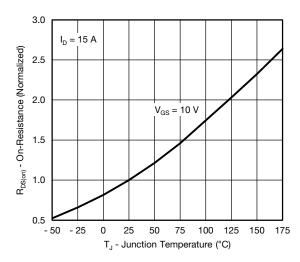
Gate Charge



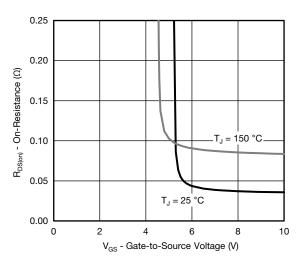
Source Drain Diode Forward Voltage



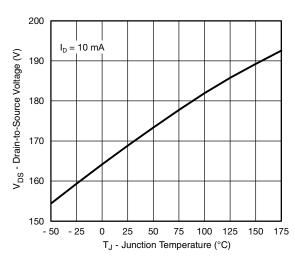
Threshold Voltage



On-Resistance vs. Junction Temperature



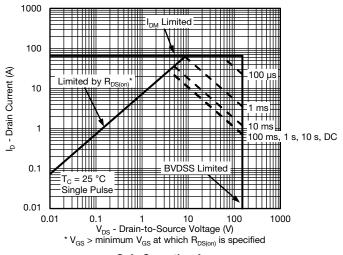
On-Resistance vs. Gate-to-Source Voltage



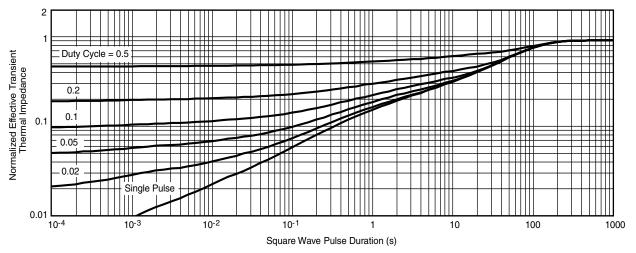
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



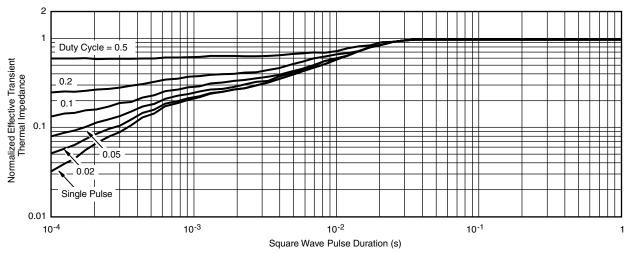
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

- Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg266974.



Vishay Siliconix

TO-220

Ordering codes for the SQ rugged series power MOSFETs in the TO-220 package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQP100N04-3m6	-	SQP100N04-3M6_GE3
SQP100P06-9m3L	-	SQP100P06-9M3L_GE3
SQP120N06-06	-	SQP120N06-06_GE3
SQP120N06-3m5L	SQP120N06-3M5L-GE3	SQP120N06-3M5L_GE3
SQP120N10-09	SQP120N10-09-GE3	SQP120N10-09_GE3
SQP120N10-3m8	SQP120N10-3M8-GE3	SQP120N10-3M8_GE3
SQP25N15-52	-	SQP25N15-52_GE3
SQP50N06-09L	SQP50N06-09L-GE3	SQP50N06-09L_GE3
SQP50P03-07	SQP50P03-07-GE3	SQP50P03-07_GE3
SQP60N06-15	SQP60N06-15-GE3	SQP60N06-15_GE3
SQP90P06-07L	SQP90P06-07L-GE3	SQP90P06-07L_GE3

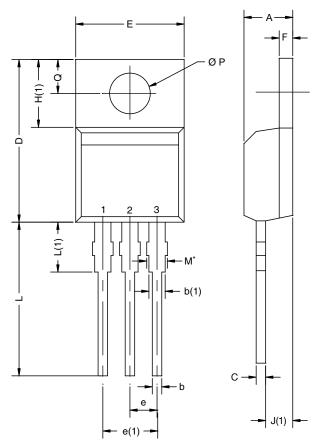
Note

a. Old ordering code is obsolete and no longer valid for new orders



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TO-220AB



		D2

	MILLIN	IETERS	INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
Е	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØΡ	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

 * M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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Revision: 02-Oct-12 Document Number: 91000

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IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

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